

## DECLARATION AND POWER OF ATTORNEY

As a below named inventor, I hereby declare that:

My residence, post office address, and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter claimed and for which a patent is sought on the invention entitled:

### **INTEGRATED CIRCUIT WITH PROTECTED IMPLANTATION PROFILES AND METHOD FOR THE FORMATION THEREOF**

the specification of which

☒ is attached hereto

☐ was filed on \_\_\_\_ as Application Serial No. \_\_\_\_ and was amended on \_\_\_\_ (if applicable).

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above.

I do not know and do not believe the same was ever known or used in the United States of America before this invention thereof or more than one year prior to this application, and that the same was not in public use or on sale in the United States of America more than one year prior to this application. I acknowledge the duty to disclose information which is known to me to be material to patentability in accordance with title 37, Code of Federal Regulations, section 1.56.

I hereby claim foreign priority benefits under Title 35, United States Code, Section 119(a)-(d) or Section 365(b) of any foreign application(s) for patent or inventor's certificate, or Section 365(a) of any PCT international application which designated at least one country other than the United States, listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

#### **Prior Foreign Application(s):**

<u>Number</u>	<u>Country</u>	<u>Day/Month/Year filed</u>	<u>Priority Claimed</u>	
			<u>Yes</u>	<u>No</u>

I hereby claim the benefit under 35 USC 119(e) of any United States provisional application(s) listed below:

#### **Prior Provisional Application(s):**

<u>Application Number</u>	<u>Filing Date</u>
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I hereby claim the benefit under Title 35, United States Code, Section 120 of any United States application(s), or Section 365(c) of any PCT international application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT international application in the manner provided by the first paragraph of Title 35, United States Code, Section 112, I acknowledge the duty to disclose material information as defined in Title 37, Code of Federal

Docket No.: 1016-024

Regulations, Section 1.56 which occurred between the filing date of the prior application and the national or PCT international filing date of this application:

Prior U.S. Application(s):

<u>Serial No.</u>	<u>Filing Date</u>	<u>Status: Patented, Pending, Abandoned</u>
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I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

I hereby revoke any previous Powers of Attorney and appoint the following attorney(s) and/or agent(s), each said individual being a member or associate of The Law Offices of Mikio Ishimaru or being employed by Chartered Semiconductor Manufacturing Ltd.:

Mikio Ishimaru	Reg. No. 27,449	William D. Zahrt II	Reg. No. 26,070
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for so long as they remain with such law offices or company with full power of substitution and revocation, to prosecute this application and to transact in connection therewith all business in the Patent and Trademark Office and before competent International Authorities; said appointment to be to the exclusion of myself and my other attorney(s); and all future correspondence should be addressed to:

Mikio Ishimaru  
The Law Offices of Mikio Ishimaru  
1110 Sunnyvale - Saratoga Rd., Suite A1  
Sunnyvale, California 94087

.....  
Inventor's signature: \_\_\_\_\_

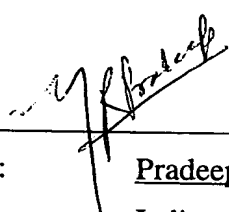
Date: 17-oct-03

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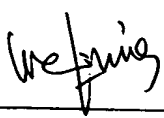
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